

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7552	(mems near2 (device package structure packaging))(micro\$2 near1 machine\$2 near1 electromechanical near1 (structure device sensor system))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 10:55
L2	5638	1 and (substrate carrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 10:56
L3	5402	2 and (method process)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 10:56
L4	1138	3 and ring	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 10:57
L5	92	3 and ((cap lid cover) near4 ring)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 13:28
L6	60	5 and (sacrificial (photoresist (photo adj resist)(silicon adj dioxide) (amorphous adj silicon)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 13:28
L7	48	6 and (transparent glass (micro adj mirror))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 13:30
L8	12	6 not 7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 13:26
L9	2519	3 and (cap lid cover)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 13:28

L10	718	9 and ring	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 13:28
L11	402	10 and (sacrificial (photoresist (photo adj resist)(silicon adj dioxide) (amorphous adj silicon)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 13:29
L12	299	10 and ((etching etched remove removing removed) with (sacrificial (photoresist (photo adj resist)(silicon adj dioxide) (amorphous adj silicon))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 17:08
L13	246	10 and ((etching etched remove removing removed) near3 (sacrificial (photoresist (photo adj resist)(silicon adj dioxide) (amorphous adj silicon))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:38
L14	155	13 and (transparent window glass (micro adj mirror))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:34
L15	134	14 not 6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 13:31
L16	2	("6635509").URPN.	USPAT	OR	ON	2005/05/20 14:11
L17	1	("6808954").URPN.	USPAT	OR	ON	2005/05/20 14:16
L18	3	("5589082" "6174820" "6635509").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/20 14:16
L19	10	("5589082" "5668033" "5783749" "5937275" "5952572" "6140144" "6232150" "6265246" "6297072" "6335224").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/20 14:17
L20	32	("5589082").URPN.	USPAT	OR	ON	2005/05/20 15:25

L21	62	(US-20030036214-\$ or US-20030209073-\$ or US-20050091843-\$ or US-20050077612-\$).did. or (US-4372173-\$ or US-4882933-\$ or US-5005413-\$ or US-5025346-\$ or US-5109175-\$ or US-5392650-\$ or US-5396797-\$ or US-5491604-\$ or US-5500549-\$ or US-5559291-\$ or US-5627314-\$ or US-5731703-\$ or US-5869760-\$ or US-5886259-\$ or US-5948981-\$ or US-5948982-\$ or US-5962784-\$ or US-5962786-\$ or US-5996411-\$ or US-6122961-\$ or US-6250156-\$ or US-6257060-\$ or US-6273514-\$ or US-6276203-\$ or US-6285111-\$ or US-6295870-\$).did. or (US-6365442-\$ or US-6392220-\$ or US-6505512-\$ or US-6634231-\$ or US-6642067-\$ or US-6662655-\$ or US-6684698-\$ or US-6753638-\$ or US-6838762-\$ or US-6778046-\$ or US-6784020-\$ or US-6768207-\$ or US-6764875-\$ or US-6479320-\$ or US-6452238-\$ or US-6303986-\$ or US-6025767-\$ or US-6815739-\$ or US-6849471-\$ or US-6848771-\$ or US-6822326-\$ or US-6713828-\$ or US-6635509-\$ or US-6777263-\$ or US-6297072-\$ or US-6265246-\$ or US-6232150-\$).did. or (US-6140144-\$ or US-5783749-\$ or US-5589082-\$ or US-6808954-\$ or US-6628177-\$).did.	US-PGPUB; USPAT	OR	ON	2005/05/20 15:30
L22	14	13 and ((bonding bonded) near1 ring)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:35
L23	21	13 and ((bonding bonded) near3 ring)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:36
L24	168	10 and ((etching etched remove removing removed) near2 (sacrificial (photoresist (photo adj resist)(silicon adj dioxide) (amorphous adj silicon))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:38

L25	139	24 not 21 not 22 not 23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:40
L26	139	25 and (wafer semiconductor silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:40
L27	133	25 and (wafer semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:41
L28	133	27 not 21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:41
L29	23	"5430421"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/05/20 15:51
L30	7	("3974468" "4063203" "4899439" "4909909" "4915983" "4920639" "5092032").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/20 15:54
L31	11	"5783749"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:55
L32	3	("4655081" "5329815" "5533394").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/20 15:55
L33	673	10 and (etching etched remove removing removed)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 17:08
L34	401	11 and (etching etched remove removing removed)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 17:09
L35	31	34 and (vacuum near2 sealing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 17:17

L36	53	12 not 13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 17:17
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L2	0	1 and (mems near1 (device package structure))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 10:40
L3	2	1 and mems	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 10:40
L4	22	("6297072").URPN.	USPAT	OR	ON	2005/05/20 10:41
L5	9	("4769344" "5296408" "5317922" "5335550" "5430421" "5602385" "5610431" "5929728" "6124145").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/20 10:48